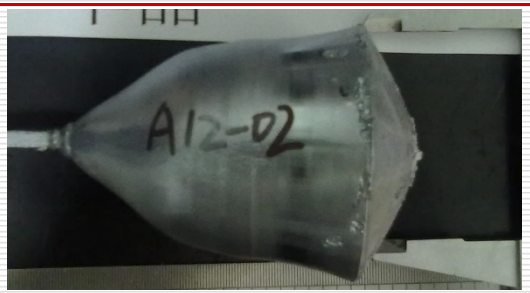
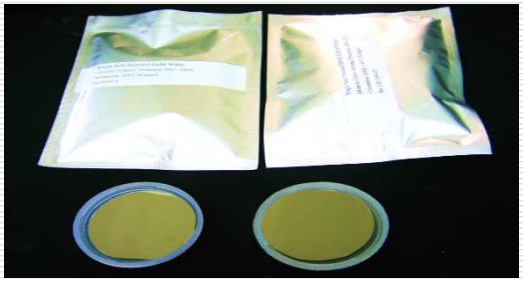
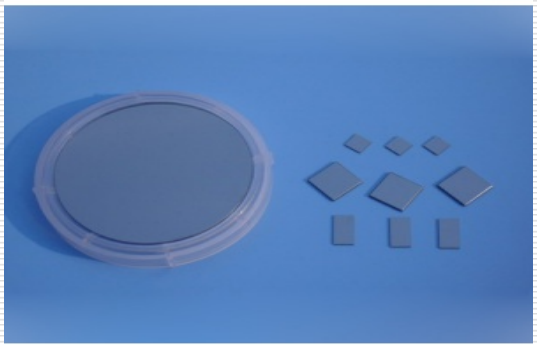
InAs Product

InAs single crystal has high electron mobility and is suitable for high-speed electronic devices. It is also an ideal material for making infrared windows.

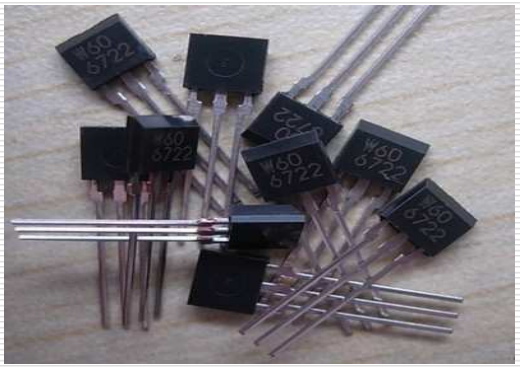
As the substrate, a heterojunction superlattice such as InAsSb, InAsPSb, InNAsSb or the like can be grown for a long-wavelength infrared light-emitting device, a quantum cascade laser, or the like.







Source or substrate of the laser



Hall device

InAsInfrared detector

InAs Product

Electrical parameters				
Dopant	Type	Carrier Con(cm-3)	Mobility ($cm^2/V.s$)	EPD (cm^{-2})
Undoped	n-型	$<5x10^{16}$	$\geq 2x10^4$	≤50000
Doped-Sn	n-型	$(5-20)x10^{17}$	＞2000	≤50000
Doped-S	n-型	$(3-80)\ x10^{17}$	＞2000	≤50000
Doped-Zn	P-型	$(3-80)\ x10^{17}$	60～300	≤50000

InAs Product

items	2″	3″
Dia (mm)	50.5±0.5	76.2±0.5
Thickness (um)	500±25	600±25
Orientation	(100)/(111)	(100)/(111)
Deviation	±0.5°	±0.5°
Major (mm)	16±2	22±2
Minor (mm)	8±1	11±1
TTV(um)	＜10	＜10
Bow(um)	＜10	＜10
Warp(um)	＜15	＜15
Surface Finish	Single-side polished/Double-sides polished	Single-side polished/Double-sides polished